



STGB8NC60K - STGD8NC60K STGP8NC60K

N-channel 600V - 8A - D²PAK / DPAK / TO-220
Short circuit rated PowerMESH™ IGBT

Features

Type	V _{CES}	V _{CE(sat) Typ @25°C}	I _C @100°C
STGB8NC60K	600V	2.2V	8A
STGD8NC60K	600V	2.2V	8A
STGP8NC60K	600V	2.2V	8A

- Lower on voltage drop (V_{cesat})
- Lower C_{RES} / C_{IES} ratio (no cross-conduction susceptibility)
- Very soft ultra fast recovery antiparallel diode
- Short circuit withstand time 10µs

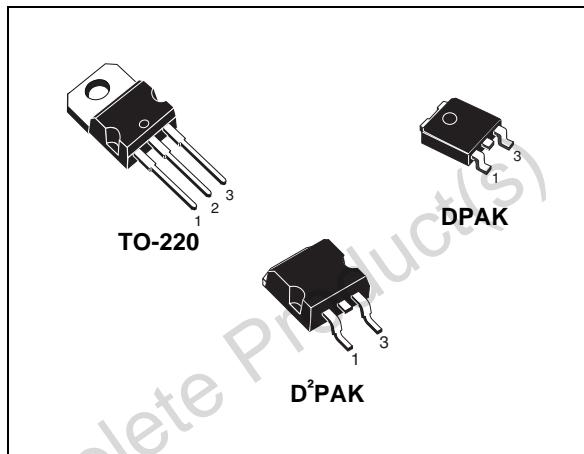
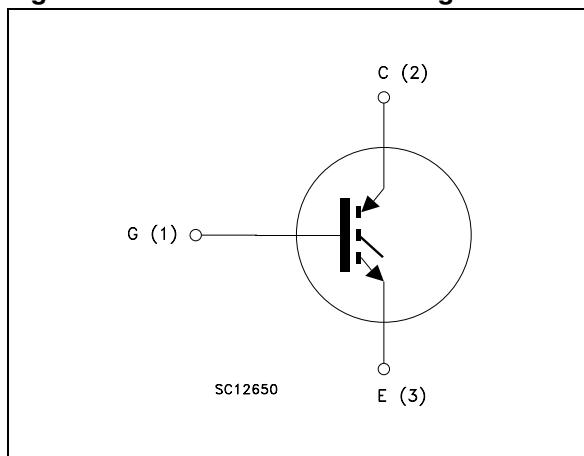


Figure 1. Internal schematic diagram



Description

Using the latest high voltage technology based on a patented strip layout, STMicroelectronics has designed an advanced family of IGBTs, the PowerMESH™ IGBTs, with outstanding performances. The suffix "K" identifies a family optimized for high frequency motor control applications with short circuit withstand capability.

Table 1. Device summary

Order codes	Marking	Package	Packaging
STGB8NC60K	GB8NC60K	D ² PAK	Tape & reel
STGD8NC60K	GD8NC60K	DPAK	Tape & reel
STGP8NC60K	GP8NC60K	TO-220	Tube

Contents

1	Electrical ratings	3
2	Electrical characteristics	4
2.1	Electrical characteristics (curves)	6
3	Test circuit	9
4	Package mechanical data	10
5	Packaging mechanical data	14
6	Revision history	16

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		D ² PAK/TO-220	DPAK	
V_{CES}	Collector-emitter voltage ($V_{GS} = 0$)	600		V
$I_C^{(1)}$	Collector current (continuous) at $T_C = 25^\circ\text{C}$	15		A
$I_C^{(1)}$	Collector current (continuous) at $T_C = 100^\circ\text{C}$	8		A
$I_{CP}^{(2)}$	Pulsed collector current	30		A
V_{GE}	Gate-emitter voltage	± 20		V
P_{TOT}	Total dissipation at $T_C = 25^\circ\text{C}$	65	62	W
T_j	Operating junction temperature	– 55 to 150		$^\circ\text{C}$
T_{scw}	Short circuit withstand time	10		μs

1. Calculated according to the iterative formula:

$$I_C(T_C) = \frac{T_{JMAX} - T_C}{R_{THJ-C} \times V_{CESAT(MAX)}(T_C; I_C)}$$

2. Pulse width limited by max junction temperature

Table 3. Thermal resistance

Symbol	Parameter		Value	Unit
R _{thj-case}	Thermal resistance junction-case max	TO-220 / D ² PAK	1.9	$^\circ\text{C/W}$
		DPAK	2.0	$^\circ\text{C/W}$
R _{thj-amb}	Thermal resistance junction-ambient Max		62.5	$^\circ\text{C/W}$

2 Electrical characteristics

($T_{CASE}=25^{\circ}\text{C}$ unless otherwise specified)

Table 4. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{BR(CES)}$	Collector-emitter breakdown voltage	$I_C = 1\text{mA}$, $V_{GE} = 0$	600			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_{GE} = 15\text{V}$, $I_C = 3\text{A}$ $V_{GE} = 15\text{V}$, $I_C = 3\text{A}$, $T_c = 125^{\circ}\text{C}$		2.2 1.8	2.75	V V
$V_{GE(th)}$	Gate threshold voltage	$V_{CE} = V_{GE}$, $I_C = 250\text{\mu A}$	4.5		6.5	V
I_{CES}	Collector cut-off current ($V_{GE} = 0$)	$V_{CE} = \text{Max rating}$, $T_C = 25^{\circ}\text{C}$ $V_{CE} = \text{Max rating}$, $T_C = 125^{\circ}\text{C}$			150 1	μA mA
I_{GES}	Gate-emitter leakage current ($V_{CE} = 0$)	$V_{GE} = \pm 20\text{V}$, $V_{CE} = 0$			± 100	nA
g_{fs}	Forward transconductance	$V_{CE} = 15\text{V}$, $I_C = 3\text{A}$		15		s

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{ies}	Input capacitance			380		pF
C_{oes}	Output capacitance	$V_{CE} = 25\text{V}$, $f = 1\text{MHz}$,		46		pF
C_{res}	Reverse transfer capacitance	$V_{GE} = 0$		8.5		pF
Q_g	Total gate charge			19		nC
Q_{ge}	Gate-emitter charge	$V_{CE} = 390\text{V}$, $I_C = 3\text{A}$,		5		nC
Q_{gc}	Gate-collector charge	$V_{GE} = 15\text{V}$, (see Figure 18)		9		nC

Table 6. Switching on/off (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r $(di/dt)_{on}$	Turn-on delay time Current rise time Turn-on current slope	$V_{CC} = 390V, I_C = 3A$ $R_G = 10\Omega, V_{GE} = 15V,$ $T_j = 25^\circ C$ (see Figure 19)		17 6 655		ns ns A/μs
$t_{d(on)}$ t_r $(di/dt)_{on}$	Turn-on delay time Current rise time Turn-on current slope	$V_{CC} = 390V, I_C = 3A$ $R_G = 10\Omega, V_{GE} = 15V,$ $T_j = 125^\circ C$ (see Figure 19)		16.5 6.5 575		ns ns A/μs
$t_r(V_{off})$ $t_{d(off)}$ t_f	Off voltage rise time Turn-off delay time Current fall time	$V_{CC} = 390V, I_C = 3A,$ $R_{GE} = 10\Omega, V_{GE} = 15V,$ $T_j = 25^\circ C$ (see Figure 19)		33 72 82		ns ns ns
$t_r(V_{off})$ $t_{d(off)}$ t_f	Off voltage rise time Turn-off delay time Current fall time	$V_{CC} = 390V, I_C = 3A,$ $R_{GE} = 10\Omega, V_{GE} = 15V,$ $T_j = 125^\circ C$ (see Figure 19)		60 106 136		ns ns ns

Table 7. Switching energy (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$E_{on}^{(1)}$ $E_{off}^{(2)}$ E_{ts}	Turn-on switching losses Turn-off switching losses Total switching losses	$V_{CC} = 390V, I_C = 3A$ $R_G = 10\Omega, V_{GE} = 15V, T_j = 25^\circ C$ (see Figure 19)		55 85 140		μJ μJ μJ
$E_{on}^{(1)}$ $E_{off}^{(2)}$ E_{ts}	Turn-on switching losses Turn-off switching losses Total switching losses	$V_{CC} = 390V, I_C = 3A$ $R_G = 10\Omega, V_{GE} = 15V,$ $T_j = 125^\circ C$ (see Figure 19)		87 162 249		μJ μJ μJ

1. E_{on} is the turn-on losses when a typical diode is used in the test circuit in figure 2. If the IGBT is offered in a package with a co-pak diode, the co-pak diode is used as external diode. IGBTs & Diode are at the same temperature ($25^\circ C$ and $125^\circ C$)
2. Turn-off losses include also the tail of the collector current

2.1 Electrical characteristics (curves)

Figure 2. Output characteristics

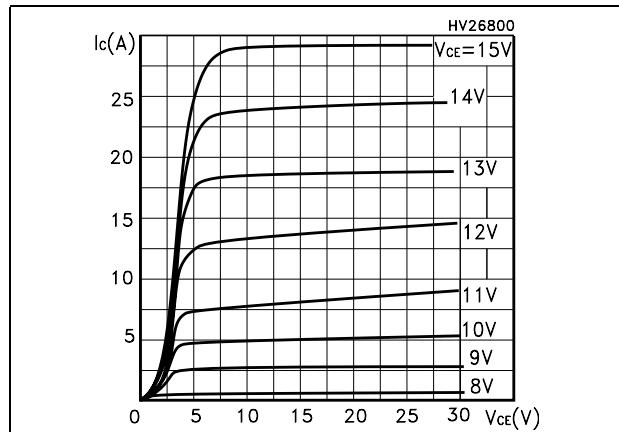


Figure 3. Transfer characteristics

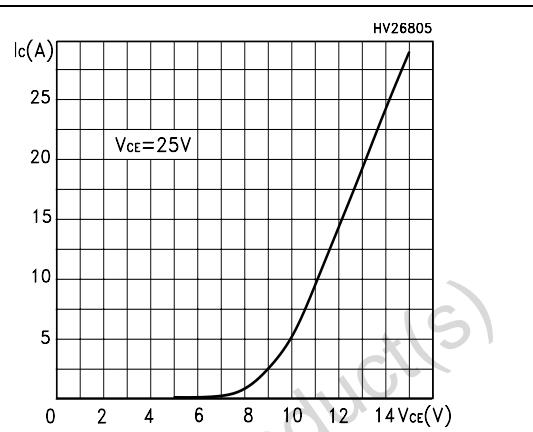


Figure 4. Transconductance

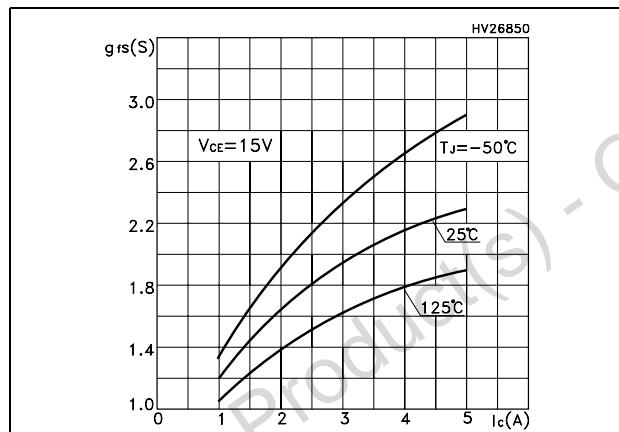


Figure 5. Collector-emitter on voltage vs temperature

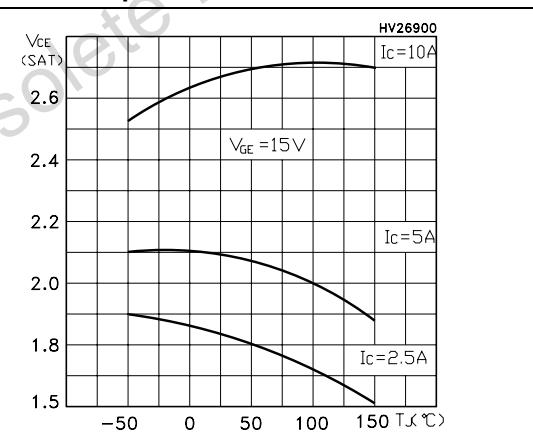


Figure 6. Gate charge vs gate-source voltage

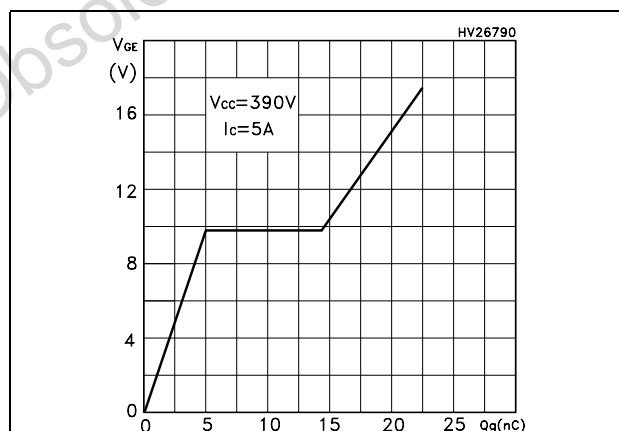


Figure 7. Capacitance variations

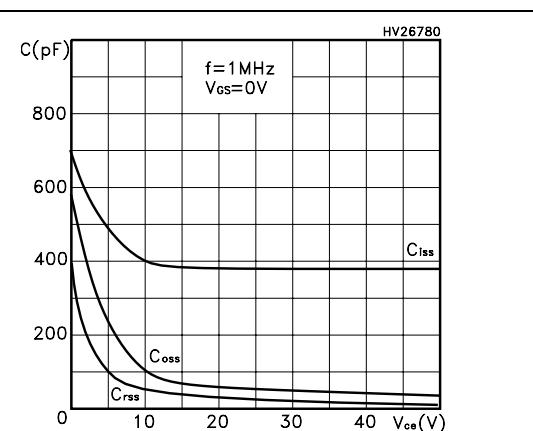
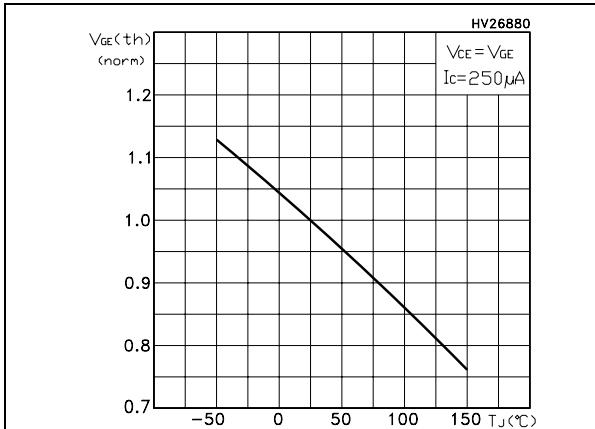
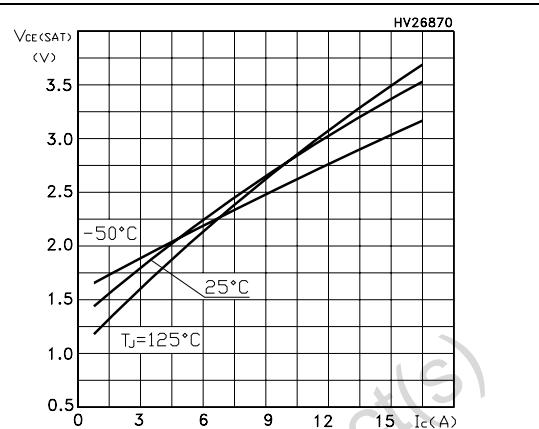
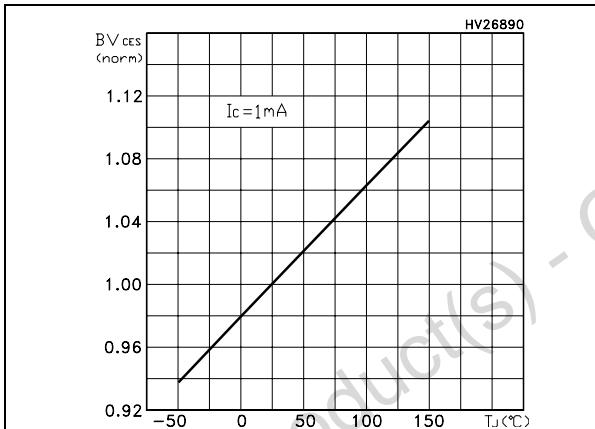
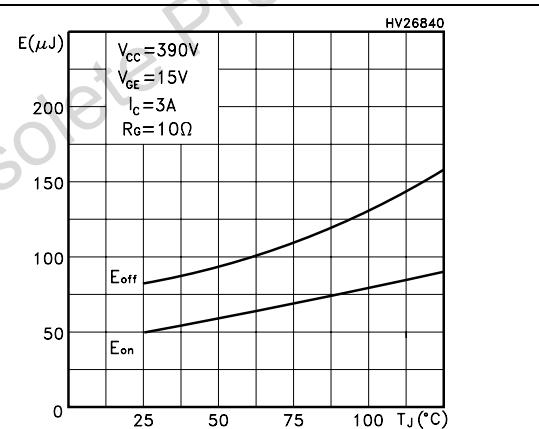
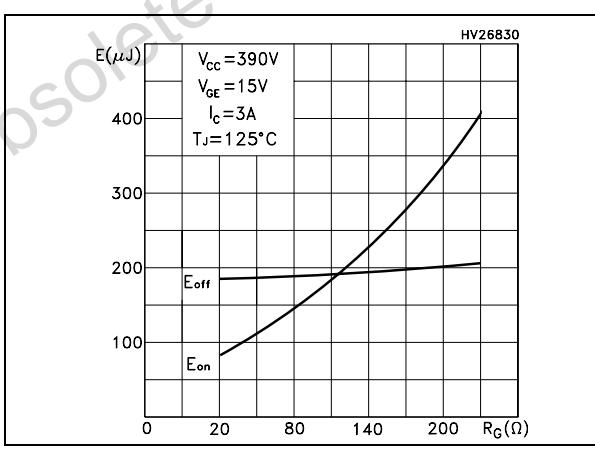
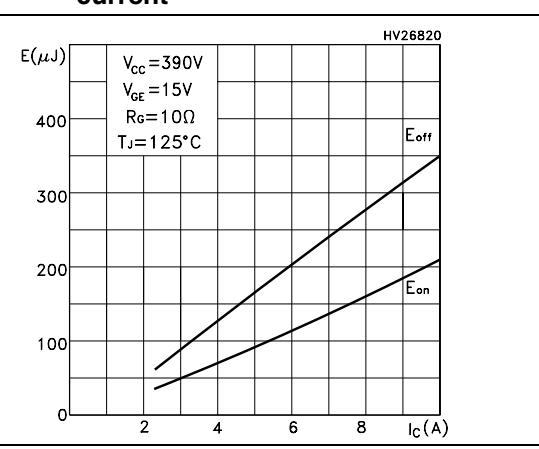


Figure 8. Normalized gate threshold voltage vs temperature**Figure 9. Collector-emitter on voltage vs collector current****Figure 10. Normalized breakdown voltage vs temperature****Figure 11. Switching losses vs temperature****Figure 12. Switching losses vs gate resistance****Figure 13. Switching losses vs collector current**

**Figure 14. Thermal impedance for TO-220/
D²PAK**

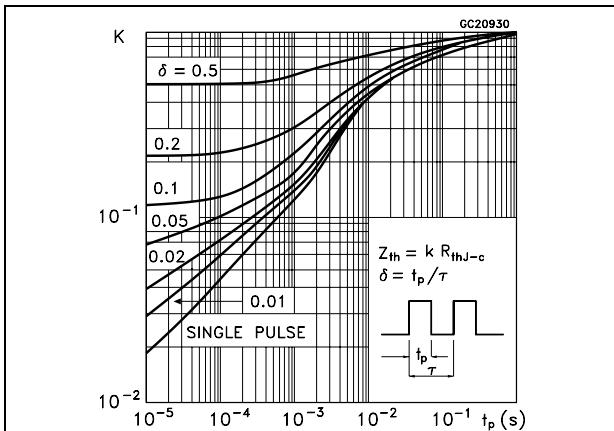


Figure 15. Turn-off SOA

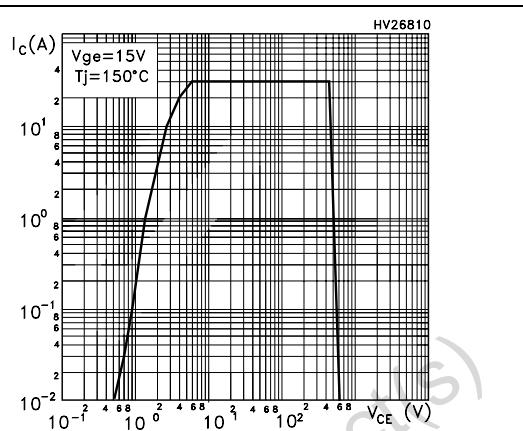
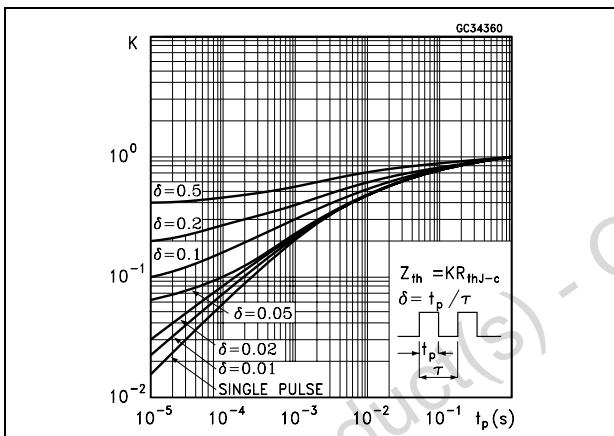


Figure 16. Thermal impedance for DPAK



3 Test circuit

Figure 17. Test circuit for inductive load switching

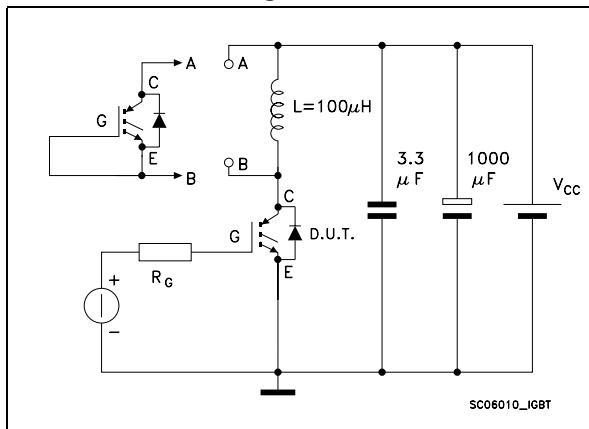


Figure 19. Switching waveform

Figure 18. Gate charge test circuit

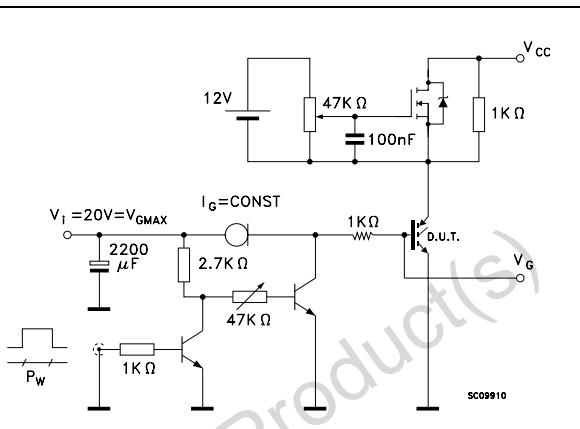
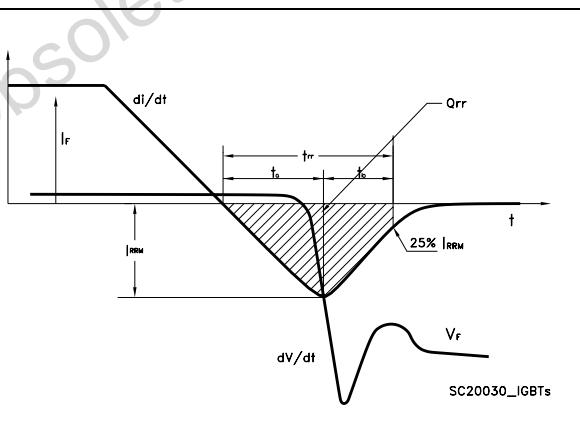
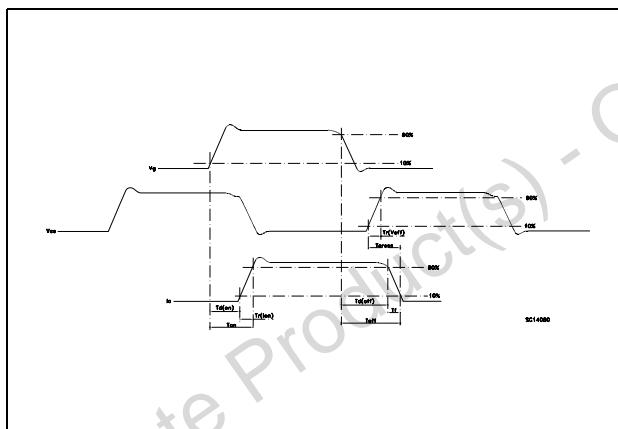


Figure 20. Diode recovery time waveform

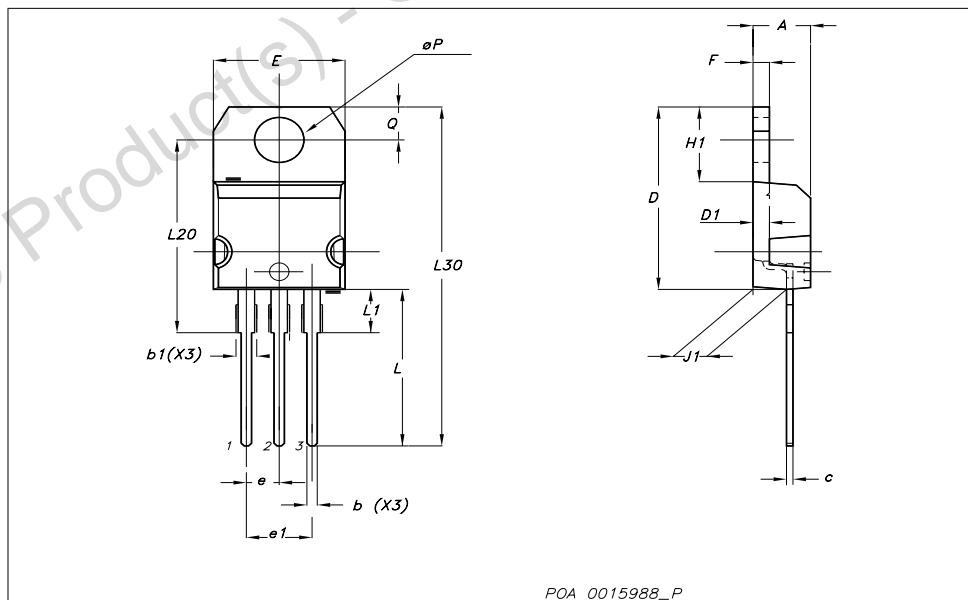


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark.
ECOPACK specifications are available at: www.st.com

TO-220 mechanical data

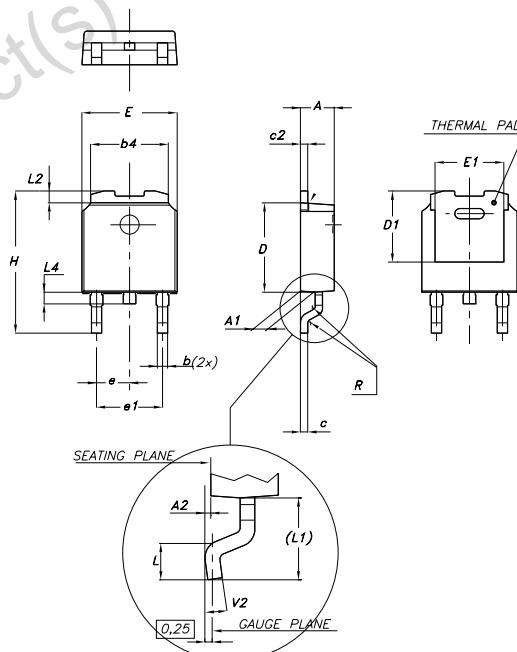
Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.6		0.62
D1		1.27			0.050	
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.051
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
$\varnothing P$	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



POA 0015988_P

DPAK MECHANICAL DATA

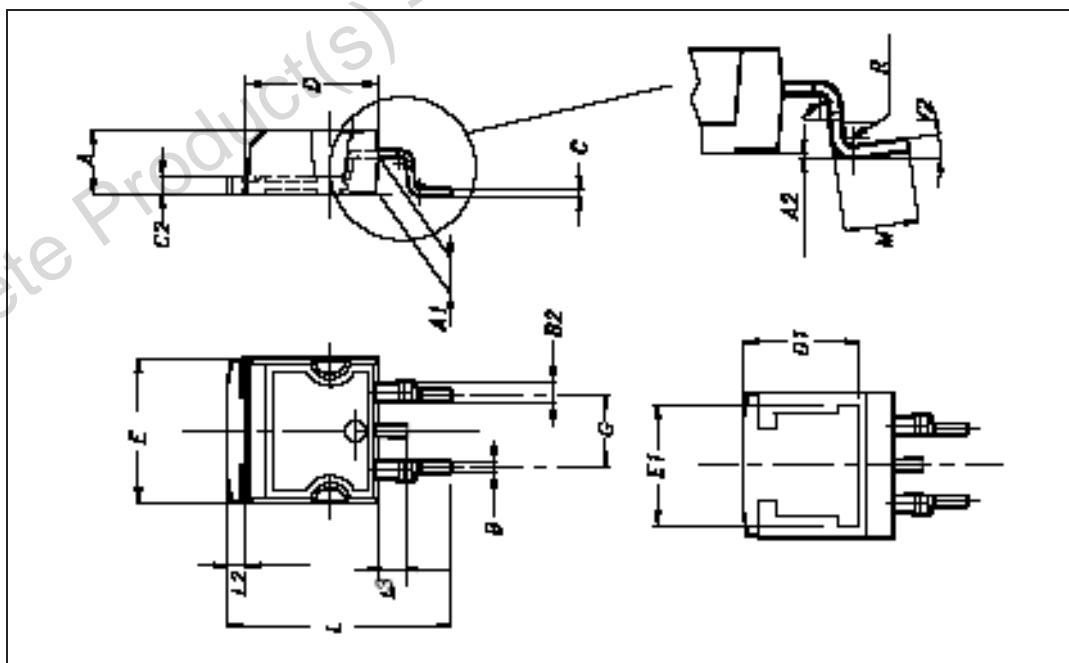
DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.9	0.025		0.035
b4	5.2		5.4	0.204		0.212
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
D1		5.1			0.200	
E	6.4		6.6	0.252		0.260
E1		4.7			0.185	
e		2.28			0.090	
e1	4.4		4.6	0.173		0.181
H	9.35		10.1	0.368		0.397
L	1			0.039		
(L1)		2.8			0.110	
L2		0.8			0.031	
L4	0.6		1	0.023		0.039
R		0.2			0.008	
V2	0°		8°	0°		8°



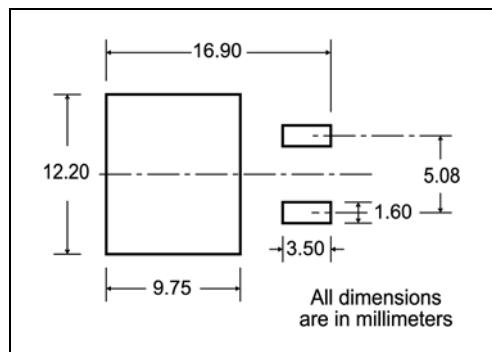
0068772-F

D²PAK mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		0.409
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.50		0.55
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0°		4°			



5 Packaging mechanical data

D²PAK FOOTPRINT**TAPE AND REEL SHIPMENT**

REEL MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956

BASE QTY **BULK QTY**

1000	1000
------	------

10 pitches cumulative tolerance on tape + / - 0.2 mm

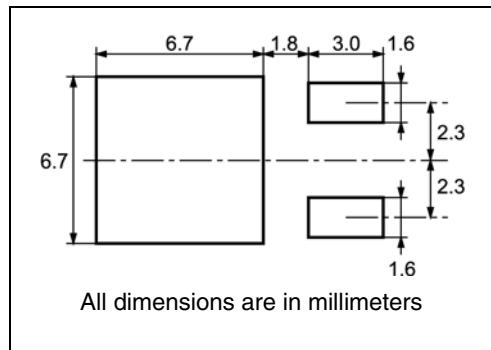
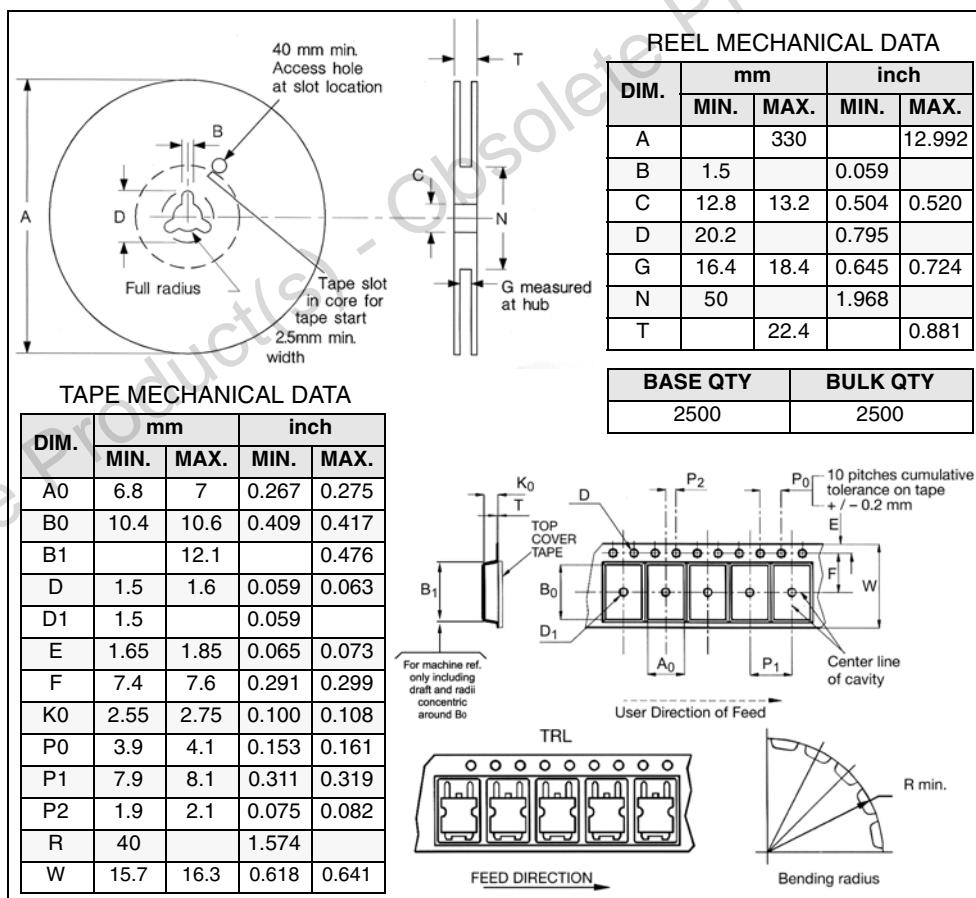
Center line of cavity

User Direction of Feed

FEED DIRECTION →

Bending radius R min.

* on sales type

DPAK FOOTPRINT**TAPE AND REEL SHIPMENT**

6 Revision history

Table 8. Document revision history

Date	Revision	Changes
02-Oct-2007	1	First release

STGB8NC60K - STGD8NC60K - STGP8NC60K

Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY AN AUTHORIZED ST REPRESENTATIVE, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2007 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com

